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The development of MOVPE InAs/GaInSb strained layer superlattice structures

InAs/GaInSb strained layer superlattice structures were discovered to have the same detectivities as HgCdTe ternary alloys of the same threshold energy at room temperature. This makes these superlattices suitable replacements for HgCdTe, which presents some technological difficulties. In this paper the optical and structural properties of GaInSb and GaInSb/GaSb quantum wells grown by metal-organic vapour phase epitaxy (MOVPE) are discussed.

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